

# PSMN8R5-40MSD

N-channel 40 V, 8.5 m $\Omega$ , standard level MOSFET in LFPAK33 using NextPower-S3 technology

10 February 2020

**Product data sheet** 

### 1. General description

60 A, standard level N-channel enhancement mode MOSFET in 175 °C LFPAK33 package using advanced TrenchMOS Superjunction technology. This product has been designed and qualified for high efficiency applications at high switching frequencies.

### 2. Features and benefits

- Avalanche rated, 100% tested
- NextPower-S3 technology delivers 'superfast switching with soft body-diode recovery'
- Low Q<sub>RR</sub>, Q<sub>G</sub> and Q<sub>GD</sub> for high system efficiency, especially at high switching frequencies
- · Low spiking and ringing for low EMI designs
- High reliability clip bonded and solder die attach Mini Power SO8 package; no glue, no wire bonds, qualified to 175 °C
- Exposed leads can be wave soldered, visual solder joint inspection and high quality solder joints
- · Low parasitic inductance and resistance

### 3. Applications

- Secondary side synchronous rectification
- DC-to-DC converters
- Brushless DC motor drive
- LED lighting

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	40	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	-	60	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	59	W
Tj	junction temperature			-55	-	175	°C
Static characte	ristics			,			
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 15 A; $T_j$ = 25 °C; Fig. 10		-	7.4	8.5	mΩ
Dynamic characteristics							
$Q_{GD}$	gate-drain charge	I <sub>D</sub> = 15 A; V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 10 V;		0.6	2	4	nC
Q <sub>G(tot)</sub>	total gate charge	Fig. 12; Fig. 13		9	13.4	19	nC

<sup>[1] 60</sup>A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.



# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		D
2	S	source		
3	S	source		G—(F)
4	G	gate		mbb076 S
mb	D	Mounting base; connected to drain	1 2 3 4 LFPAK33 (SOT1210)	

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	ber Package					
	Name	Description	Version			
PSMN8R5-40MSD	LFPAK33	Plastic, single ended surface mounted package (LFPAK33); 8 leads; 0.65 mm pitch	SOT1210			

## 7. Marking

#### **Table 4. Marking codes**

Type number	Marking code
PSMN8R5-40MSD	8D5S40

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	40	V
$V_{DSM}$	peak drain-source voltage	$t_p \le 20 \text{ ns}; f \le 500 \text{ kHz}; E_{DS(AL)} \le 200 \text{ nJ};$ pulsed		-	45	V
$V_{DGR}$	drain-gate voltage	25 °C ≤ $T_j$ ≤ 175 °C; $R_{GS}$ = 20 kΩ		-	40	V
$V_{GS}$	gate-source voltage			-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	59	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	60	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>		-	42	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$ ; Fig. 3		-	239	А
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-drain	n diode			'	•	•
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	59	А

Symbol	Parameter	Conditions		Min	Max	Unit
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 °C$		-	239	А
Avalanche r	uggedness			'		
E <sub>DS(AL)S</sub>	source avalanche energy	$I_D$ = 22 A; $V_{sup} \le 40$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped; $t_p$ = 80 μs	[2]	-	46	mJ
		$I_D$ = 15 A; $V_{sup} \le 40$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped; $t_p$ = 180 μs	[2]	-	70	mJ

- [1] 60A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.
- [2] Protected by 100% test

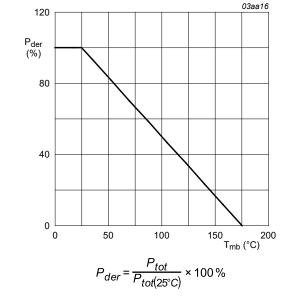
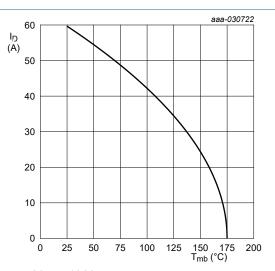


Fig. 1. Normalized total power dissipation as a function of mounting base temperature



 $V_{GS} \ge 10 \text{ V}$  (1) 60A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

Fig. 2. Continuous drain current as a function of mounting base temperature

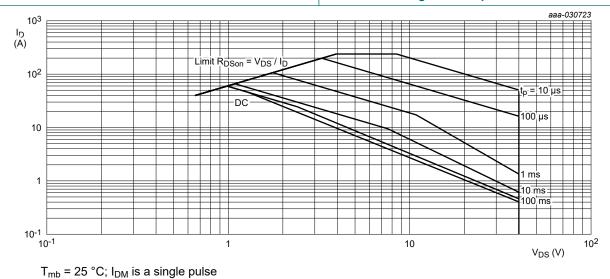


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	Fig. 4	-	2.33	2.56	K/W
R <sub>th(j-a)</sub>	thermal resistance from	Fig. 5	-	50	-	K/W
junction to ambient	Fig. 6	-	130	-	K/W	

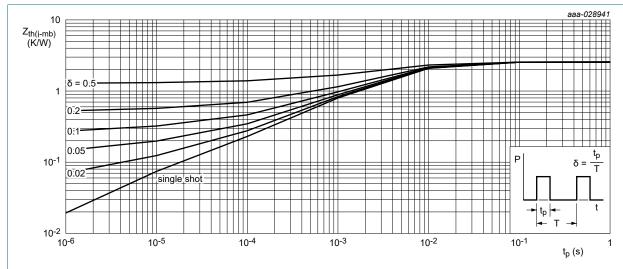


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

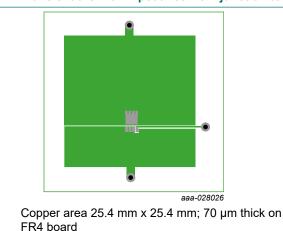
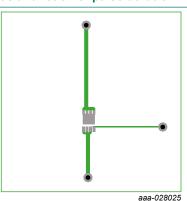


Fig. 5. PCB layout for thermal resistance from junction to ambient



70 µm thick copper on FR4 board

Fig. 6. PCB layout with minimum footprint for thermal resistance from junction to ambient

### 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static characteristics							
- (DIX)DOO	drain-source	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C		40	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$		36	-	-	V

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$		2.4	3.12	3.6	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	25 °C ≤ T <sub>j</sub> ≤ 150 °C		-	-5.9	-	mV/K
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C		-	0.01	1	μΑ
		V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C		-	1	-	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C		-	2	100	nA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C		-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ Fig. 10		-	7.4	8.5	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 175 °C;$ Fig. 11		-	-	16.5	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz; T <sub>j</sub> = 25 °C		0.3	0.8	2	Ω
Dynamic cha	racteristics		•	<u> </u>			
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 15 A; V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 10 V; Fig. 12; Fig. 13		9	13.4	19	nC
		I <sub>D</sub> = 0 A; V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 10 V		-	8.8	-	nC
$Q_{GS}$	gate-source charge	I <sub>D</sub> = 15 A; V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 10 V;		2.7	4.5	6.8	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge	Fig. 12; Fig. 13		1.7	2.9	4.4	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge			1	1.7	2.6	nC
Q <sub>GD</sub>	gate-drain charge			0.6	2	4	nC
$V_{GS(pl)}$	gate-source plateau voltage	I <sub>D</sub> = 15 A; V <sub>DS</sub> = 20 V; <u>Fig. 12</u> ; <u>Fig. 13</u>		-	4.7	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 0 V; f = 1 MHz;		614	944	1322	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 14</u>		266	409	573	pF
C <sub>rss</sub>	reverse transfer capacitance			13	44	97	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 20 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$		-	5.1	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$		-	3.2	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	8.9	-	ns
t <sub>f</sub>	fall time			-	2.8	-	ns
Q <sub>oss</sub>	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$		-	12	-	nC
Source-drain	diode						•
V <sub>SD</sub>	source-drain voltage	$I_S = 15 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 15$		-	0.85	1	V
t <sub>rr</sub>	reverse recovery time	$I_S$ = 15 A; $dI_S/dt$ = -100 A/ $\mu$ s; $V_{GS}$ = 0 V; $V_{DS}$ = 20 V; Fig. 16		-	22	-	ns
Q <sub>r</sub>	recovered charge			-	15	-	nC
t <sub>a</sub>	reverse recovery rise time			-	14	-	ns
t <sub>b</sub>	reverse recovery fall time			-	8.5	-	ns

<sup>[1]</sup> includes capacitive recovery

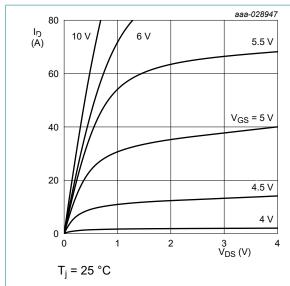


Fig. 7. Output characteristics; drain current as a function of drain-source voltage; typical values

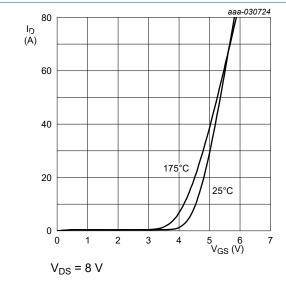


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

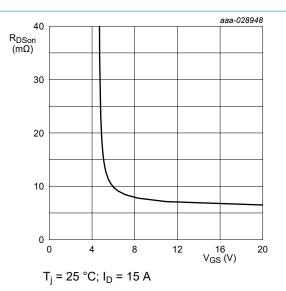


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

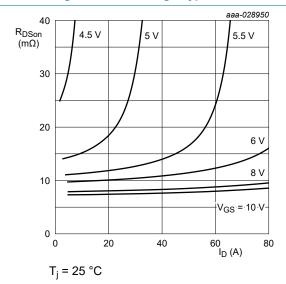


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values

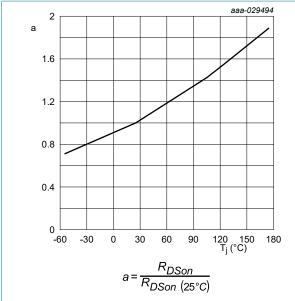


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

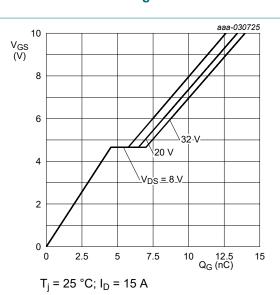


Fig. 12. Gate-source voltage as a function of gate charge; typical values

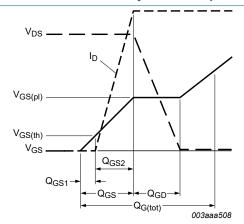
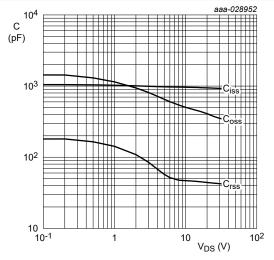


Fig. 13. Gate charge waveform definitions



 $V_{GS} = 0 V; f = 1 MHz$ 

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

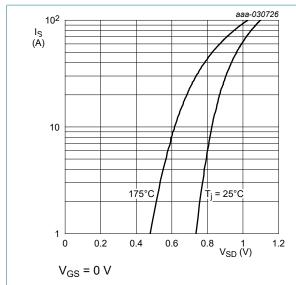


Fig. 15. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

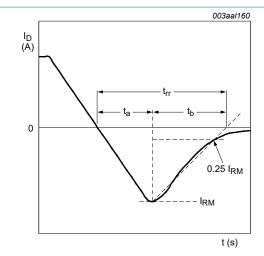


Fig. 16. Reverse recovery timing definition

## 11. Package outline

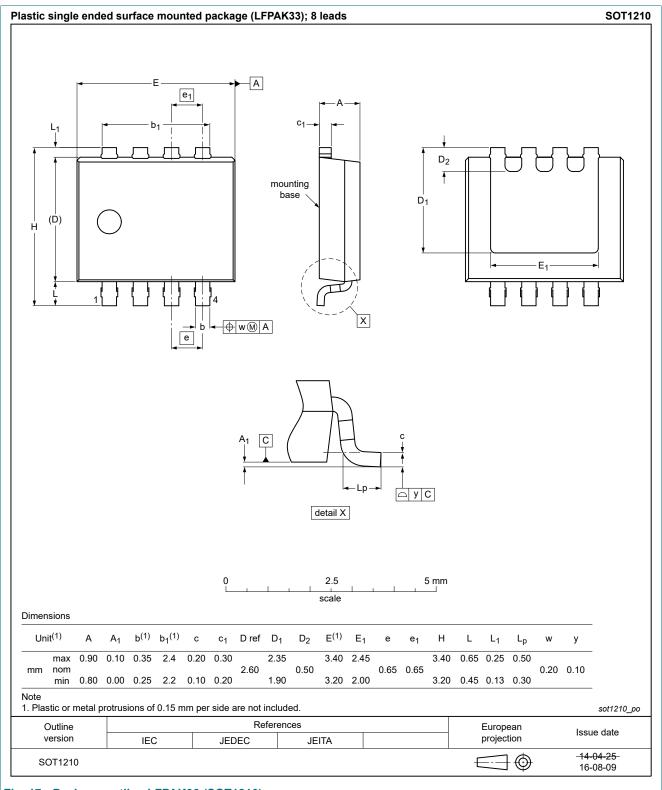
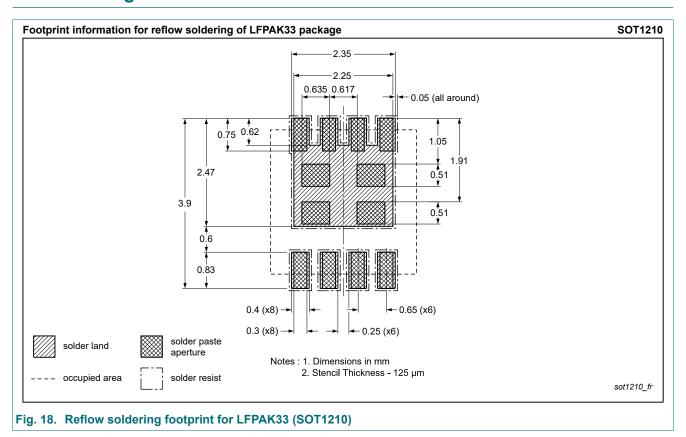


Fig. 17. Package outline LFPAK33 (SOT1210)

# 12. Soldering



### 13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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